

# Letters

## Thermogravimetric study of the non-stoichiometry of cuprite $\text{Cu}_2\text{O}$

Cuprous oxide,  $\text{Cu}_2\text{O}$ , is known to be a metal deficient p-type semi-conductor [1, 2]. Its non-stoichiometry has been investigated by gas volumetric analysis [3], thermogravimetry [4], chemical analysis of quenched samples [5], and more recently by a coulometric titration method [6]. These studies indicate that the predominant ionic defects at high temperature and high oxygen activities are neutral copper vacancies. Conversely, in low oxygen activity regions of the cuprous oxide homogeneity field, some authors [6, 7] have proposed the existence of oxygen deficient cuprite. Tretyakov *et al.*, in particular, have found deviations from stoichiometry as large as  $\gamma = 2 \times 10^{-2}$  in  $\text{Cu}_2\text{O}_{1-\gamma}$  at  $1000^\circ\text{C}$  (Fig. 1). These results are inconsistent with the p-type semi-

conductivity of  $\text{Cu}_2\text{O}$  in all its domain of existence, as found by conductivity measurements [1, 2, 8, 9]. In order to clarify this point a thermogravimetric reinvestigation has been undertaken particularly in the supposedly oxygen deficient cuprite field (Fig. 1) at as low as possible oxygen pressures to be compatible with weight change measurability.

Cuprous oxide was prepared by a floating zone technique [10, 11] from 10 mm diameter rods obtained by oxidation of high purity copper (Johnson Matthey Specpure) containing 2 ppm Ag, 1 ppm Fe and 1 ppm Si. A cylinder shaped specimen with alternate notches, 0.7 mm apart was suspended from one arm of the microbalance at the end of a thin silica wire. Experiments were carried out at five different temperatures (905, 940, 995, 1015 and  $1030^\circ\text{C}$ ) and at partial pressures of oxygen ranging from  $5 \times 10^{-2}$  to

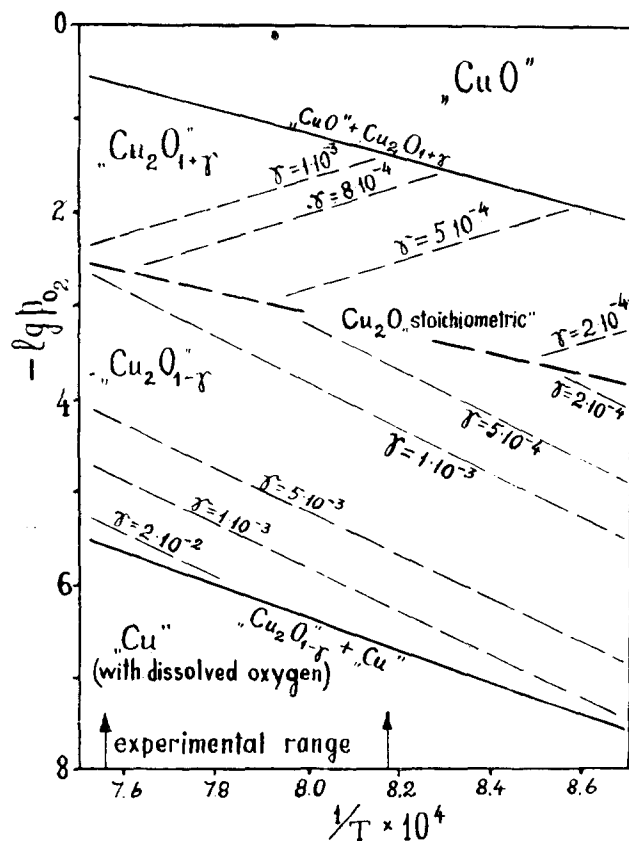


Figure 1  $P_{\text{O}_2}$  (atm),  $T$  diagram for cuprite  $\text{Cu}_2\text{O}$  [6].

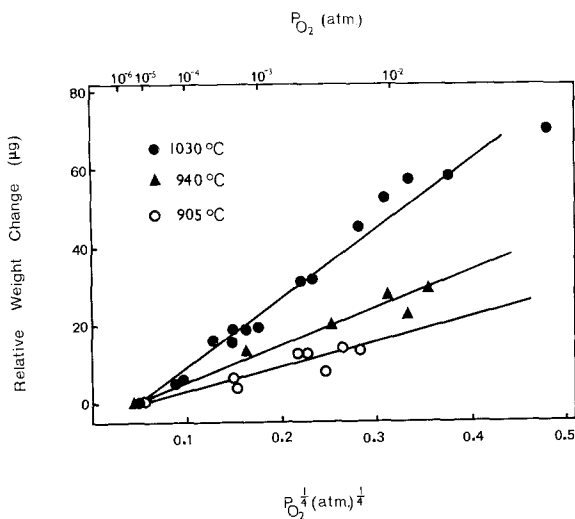


Figure 2 Weight change data as a function of  $P_{O_2}^{1/4}$ .

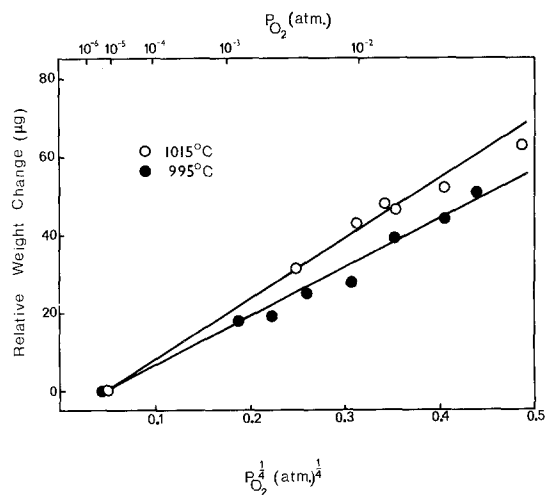


Figure 3 Weight change data as a function of  $P_{O_2}^{1/4}$ .

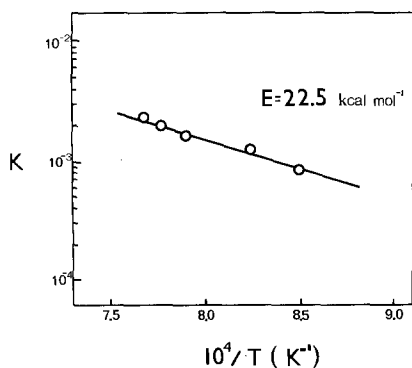


Figure 4 Arrhenius plot of mass action constant  $K$  from weight change data.

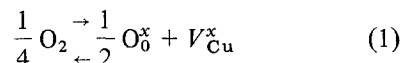
about  $5 \times 10^{-6}$  atm.

Constant  $P_{O_2}$  was achieved by a flow of an argon/oxygen mixture at a total pressure of 1 atm. This method allowed the elimination of the problems encountered at low pressures, i.e. thermomolecular flow and vaporization of  $Cu_2O$  [4]. The partial pressure of oxygen was measured at the inlet of the microbalance by a zirconium oxide oxygen gauge.

The presence of gas, flowing at about 8 litre  $h^{-1}$  around the specimen necessitated a weight correction due to minute changes of the flow rate at the different values of  $P_{O_2}$ . This correction was of  $50 \mu g l^{-1}$ . Weight losses due to vaporization of cuprite were measured at high temperatures above  $900^\circ C$ :  $0.6 \mu g h^{-1}$  at  $940^\circ C$  and  $2 \mu g h^{-1}$  at

$1030^\circ C$ . After these cumulative corrections the accuracy of the weight change measurements was estimated at  $\pm 5 \mu g$ .

Using the Kröger and Vink notation [12], the equation for copper vacancies formation is:



Thus, the deviation  $\gamma$  from stoichiometry in  $Cu_2O_{1+\gamma}$  may be written:

$$\gamma = \frac{1}{2} [V_{Cu}^x] = K \cdot P_{O_2}^{1/4} \quad (2)$$

the mass action constant  $K$  being related to the temperature by the relation

$$K = A \cdot \exp\left(-\frac{E}{RT}\right) \quad (3)$$

where  $A$  is a constant,  $T$  the absolute temperature and  $E$  the enthalpy of formation of copper vacancies.

The weight change  $\Delta W$  corresponding to a variation  $\Delta\gamma$  of the stoichiometry may then be written:

$$\Delta W = \frac{16 \cdot g}{M} \cdot \Delta\gamma = \frac{16 \cdot g}{M} K \cdot \Delta(P_{O_2}^{1/4}) \quad (4)$$

where  $g$  is the sample weight and  $M$  the molecular weight of  $Cu_2O$ .

Figs. 2 and 3 represent the relative weight

TABLE I Non-stoichiometry in  $\text{Cu}_2\text{O}_{1+\gamma}$

$P_{\text{O}_2}$ (atm)	$\gamma \times 10^4$		[5]		[6]		This work	
	[4]		900° C	1000° C	900° C	1000° C	900° C	1000° C
	900° C	1000° C	900° C	1000° C	900° C	1000° C	900° C	1000° C
$4.3 \times 10^{-2}$	—	9.1	—	11.4	7.3	13.1	—	7.4
$8.5 \times 10^{-3}$	2.8	5.9	5.4	8.3	4.6	8.7	2.3	4.9
$9.6 \times 10^{-4}$	1.6	3.2	3.0	5.2	2.8	5.1	1.3	2.9
$1 \times 10^{-5}$	—	—	—	—	-8.77	-55	0.43	0.92

change of the sample plotted versus a  $P_{\text{O}_2}^{1/4}$  dependence at different temperatures and at pressures ranging from  $5 \times 10^{-2}$  to  $5 \times 10^{-6}$  atm. From Fig. 2 it may be seen that the linear relationship extends below  $10^{-3}$  atm pressure, at which for a temperature around  $1000^\circ\text{C}$  a change of the type of non-stoichiometry should occur [6]. This would indicate that the copper vacancy defect model is valid over the whole range of oxygen partial pressure considered.

The plot of  $\log K$  versus  $1/T$  represented in Fig. 4 gives values of  $A$  and  $E$  of Equation 3:  $A = 11.9$  and  $E = 22.5 \text{ kcal mol}^{-1}$ . Using these values the deviation from stoichiometry in  $\text{Cu}_2\text{O}_{1+\gamma}$  has been calculated for different partial pressures of oxygen and compared to values derived from results and equations in [4–6] in Table I.

In conclusion it seems that the predominant ionic defect in  $\text{Cu}_2\text{O}$  at high temperature is  $V_{\text{Cu}}^\times$  down to oxygen pressures of at least  $5 \times 10^{-6}$  atm, the enthalpy of formation of copper vacancies with respect to oxygen gas at 1 atm being  $22.4 \text{ kcal mol}^{-1}$ .

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*The effect of grain size on the occurrence of cleavage fatigue failure in 316 stainless steel*

Highly reflective mirror like cleavage facets occur on the fatigue fracture surfaces of austenitic type 316 stainless steel [1]. The influence of grain size

on this failure mode has been examined for the grain sizes of 3, 20 and 37 grains/mm. Tests at 140 Hz used an Amsler vibrophore and standard compact tension [2] specimens to produce crack propagation in the stress intensity range  $\Delta K = 5 - 30 \text{ MN m}^{-3/2}$  at a stress ratio of  $R = 0.33$ .

A cleavage facet is shown for the 3 grains/mm